

10A05 THRU 10A10

TECHNICAL SPECIFICATIONS OF SILICON RECTIFIER

VOLTAGE: 50-1000V

CURRENT: 10.0A

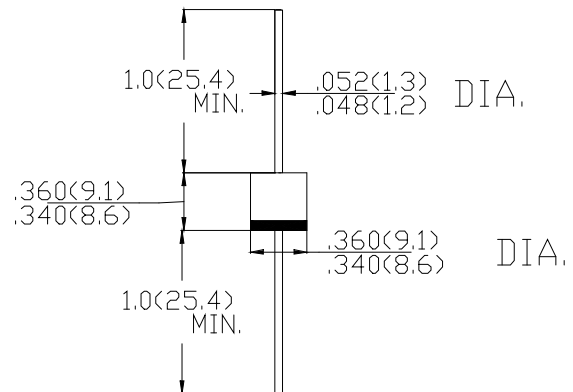
FEATURES

- Low cost
- Low leakage
- Low forward voltage drop
- High current capability
- High surge current capability

MECHANICAL DATA

- **Case:** Molded plastic
- **Epoxy:** UL94V-0 rate flame retardant
- **Lead:** MIL-STD- 202E, Method 208 guaranteed
- **Polarity:** Color band denotes cathode end
- **Mounting position:** Any
- **Weight:** 2.08 grams

R-6



Dimensions in inches and (millimeters)

MAXIMUM RATINGS AND ELECTRICAL CHARACTERISTICS

Ratings at 25°C ambient temperature unless otherwise specified.

Single phase, half wave, 60Hz, resistive or inductive load.

For capacitive load, derate current by 20%.

			10A05	10A1	10A2	10A4	10A6	10A8	10A10	
Maximum Recurrent Peak Reverse Voltage		V_{RRM}	50	100	200	400	600	800	1000	V
Maximum RMS Voltage		V_{RMS}	35	70	140	280	420	560	700	V
Maximum DC Blocking Voltage		V_{DC}	50	100	200	400	600	800	1000	V
Maximum Average Forward rectified Current at T _A =75°C		I_o	10.0							A
Peak Forward Surge Current 8.3ms single half sine-wave superimposed on rate load (JEDEC method)		I_{FSM}	300							A
Maximum Instantaneous forward Voltage at10.0A DC		V_F	1.0							V
Maximum DC Reverse Current at Rated DC Blocking Voltage	@ T _A =25°C	I_R	10							μA
	@ T _A =100°C		500							
Maximum Full Load Reverse Current Average, Full Cycle .375"(9.5mm) lead length at T _L =75°C			50							
Typical Junction Capacitance (Note)		C_J	150							pF
Typical Thermal Resistance		R_{θJA}	10							°C/W

Notes: Measured at 1MHz and applied reverse voltage of 4.0 volts